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T-33-11

Pro Electron Power Transistors

T-33-19

BD201, BD202, BD203, BD204

File Number 1282

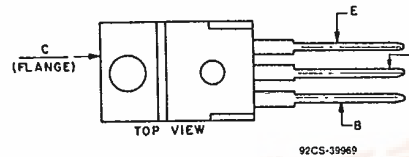
Epitaxial-Base, Silicon N-P-N and P-N-P VERSAWATT Transistors

General-Purpose Medium-Power Types for
Switching and Amplifier Applications

Features:

- Low saturation voltages
- Complementary n-p-n and p-n-p types
- Maximum safe-area-of-operation curves

TERMINAL DESIGNATIONS



JEDEC TO-220AB

The RCA-BD201 and BD203 n-p-n transistors and their complementary p-n-p types, BD202 and BD204 respectively, are epitaxial-base transistors intended for a wide variety of medium-power switching and amplifier applications, such as series and shunt regulators, and driver and output stages of high-fidelity amplifier.

All types utilize the JEDEC TO-220AB (VERSAWATT) plastic package.

MAXIMUM RATINGS, Absolute-Maximum Values:

V_{CE0}	
$V_{CE0(SUS)}$	
V_{EBO}	
I_C	
I_B	
P_T	
$T_C \leq 25^\circ C$	60
$T_C > 25^\circ C$	Derate linearly 0.48
$T_{sig} T_J$	-65 to 150
T_L	235
At distances $\geq 1/8$ in. (3.17 mm) from case for 10 s max.	

N-P-N	BD201	BD203	
P-N-P	BD202■	BD204■	
	60	80	V
	45	60	V
		5	V
		8	V
		3	A
			A
		60	W
		Derate linearly 0.48	W/°C
		-65 to 150	°C
		235	°C

■ For p-n-p devices, voltage and current values are negative.



BD201, BD202, BD203, BD204

ELECTRICAL CHARACTERISTICS, at Case Temperature (T_C)=25°C
Unless Otherwise Specified

T-33-19

CHARACTERISTIC	TEST CONDITIONS ^a				LIMITS				UNITS	
	VOLTAGE V dc			CURRENT A dc		BD201 BD202 [#]		BD203 BD204 [#]		
	V _{CB}	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	Min.		Max.
I _{CBO} T _J =150°C	40					—	1	—	1	mA
	40					—	1	—	1	
I _{CEO}		30				—	1	—	1	V
I _{EBO}			-5			—	5	—	5	
V _{CEO(sus)} ^a				0.2 ^b		45	—	60	—	V
h _{FE}		2		1 ^b		30	—	30	—	
		2		2 ^b		—	—	30	—	
		2		3 ^b		30	—	—	—	
V _{BE}		2		3 ^b		—	1.5	—	1.5	V
V _{CE(sat)}				3 ^b	0.3	—	1	—	1	
I _{S/b}		20		3		0.5	—	0.5	—	s
h _{fe} (f=1 kHz)		3		0.3		3	—	3	—	
h _{fe} (f=1 kHz)		3		0.3		25	—	25	—	
R _{θJC}						—	2.08	—	2.08	°C/W
R _{θJA}						—	70	—	70	

^aCAUTION: The sustaining voltage V_{CEO(sus)} MUST NOT be measured on a curve tracer.
^bPulsed: pulse duration = 300 μs, duty factor = 0.018.
[#]For p-n-p devices, voltage and current values are negative.

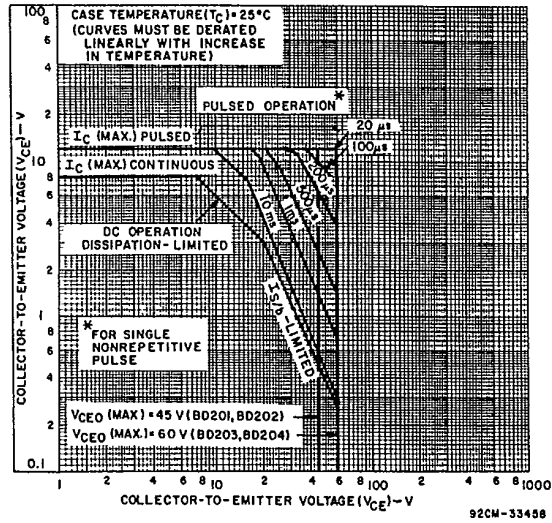


Fig. 1 — Maximum operating areas for all types ($T_C = 25^\circ\text{C}$).

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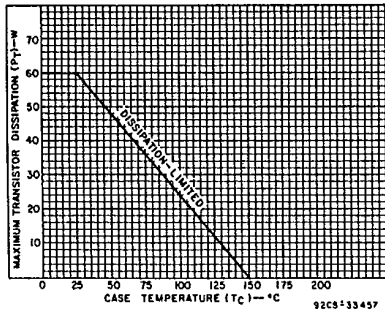


Fig. 2 - Derating curve for all types.

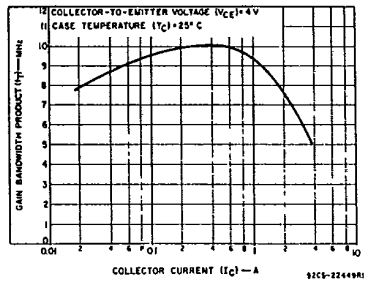


Fig. 3 - Typical gain-bandwidth product vs. collector current for all types.